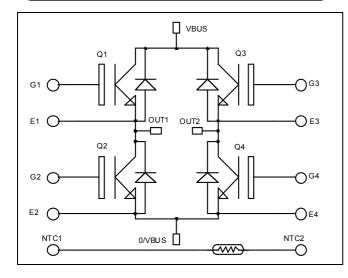
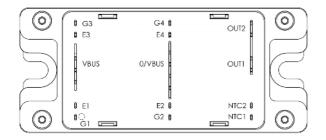


Full - Bridge Trench + Field Stop IGBT3 Power Module





## Absolute maximum ratings

#### Symbol Parameter Max ratings Unit Collector - Emitter Breakdown Voltage 1700 V<sub>CES</sub> V $T_C = 25^{\circ}C$ 75 $I_C$ Continuous Collector Current $T_C = 80^{\circ}C$ 50 Α I<sub>CM</sub> Pulsed Collector Current $T_C = 25^{\circ}C$ 100 V<sub>GE</sub> Gate - Emitter Voltage ±20 V $T_C = 25^{\circ}C$ Maximum Power Dissipation 312 W $P_D$ RBSOA Reverse Bias Safe Operating Area $T_i = 125^{\circ}C$ 100A @ 1600V

AUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

# $V_{CES} = 1700V$ $I_C = 50A$ @ Tc = 80°C

#### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

#### Features

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
    - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
  - Kelvin emitter for easy drive
    - Very low stray inductance
    - Symmetrical design
      - Lead frames for power connections
- High level of integration
- Internal thermistor for temperature monitoring

#### Benefits

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- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
  - Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

# APTGT50H170TG-Rev 2 October, 2012



## All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

## **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I <sub>CES</sub>	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1700V$				250	μA
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 50A$	$T_j = 25^{\circ}C$		2.0	2.4	V
V <sub>CE(sat)</sub>			$T_{j} = 125^{\circ}C$		2.4		v
V <sub>GE(th)</sub>	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1 mA$		5.0	5.8	6.5	V
I <sub>GES</sub>	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

## **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		4400		
C <sub>oes</sub>	Output Capacitance	$V_{CE} = 25V$		180		pF
C <sub>res</sub>	Reverse Transfer Capacitance	f = 1 MHz		150		L
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (25	5°C)	370		
Tr	Rise Time	$V_{GE} = 15V$		40		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 900V$ $I_C = 50A$		650		ns
$T_{\rm f}$	Fall Time	$R_G = 10\Omega$		180		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (12	25°C)	400		
Tr	Rise Time	$V_{GE} = 15V$		50		
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{Bus} = 900V$ $I_{C} = 50A$		800		ns
$T_{f}$	Fall Time	$R_G = 10\Omega$		300		
Eon	Turn-on Switching Energy	$V_{GE} = 15V$ $V_{Bus} = 900V$ $T_j = 12$	25°C	16		mJ
E <sub>off</sub>	Turn-off Switching Energy	$\begin{array}{c} I_C = 50A \\ R_G = 10\Omega \end{array} \qquad T_j = 12 \end{array}$	25°C	15		1113

## **Diode ratings and characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage			1700			V
I <sub>RM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> =1700V	$T_j = 25^{\circ}C$ $T_j = 125^{\circ}C$			250 500	μΑ
$I_{\rm F}$	DC Forward Current		$Tc = 80^{\circ}C$		50		А
V <sub>F</sub>	Diode Forward Voltage	$I_F = 50A$	$T_{j} = 25^{\circ}C$ $T_{j} = 125^{\circ}C$		1.8 1.9	2.2	V
t <sub>rr</sub>	Reverse Recovery Time	$I_{F} = 50A$ $V_{R} = 900V$ $di/dt = 800A/\mu s$	$T_j = 25^{\circ}C$ $T_i = 125^{\circ}C$		385 490		ns
Q <sub>rr</sub>	Reverse Recovery Charge		$T_j = 25^{\circ}C$ $T_i = 125^{\circ}C$		14 23		μC
Er	Reverse Recovery Energy		$T_j = 25^{\circ}C$ $T_j = 125^{\circ}C$		6 12		mJ



Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

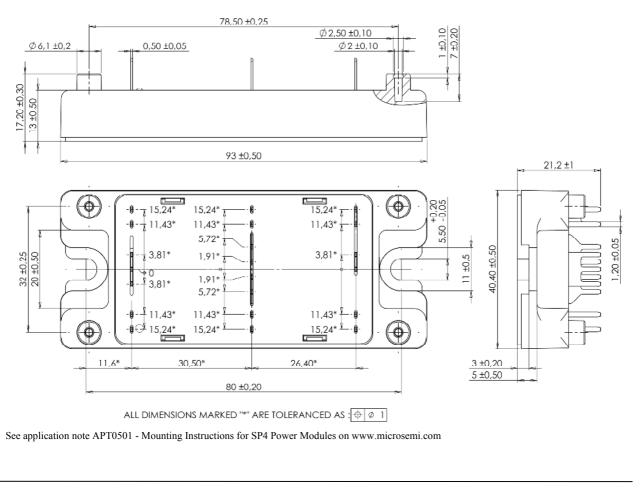
Symbol	Characteristic	Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K
-	$R_{-} = \frac{R_{25}}{1}$ T: Thermistor temperature				

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature  
R<sub>T</sub>: Thermistor value at T

### Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R <sub>thJC</sub>	Junction to Case Thermal Resistance		IGBT			0.4 °C/	°C/W
			Diode			0.7	C/ W
VISOL	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
TJ	Operating junction temperature range		-40		150		
T <sub>STG</sub>	Storage Temperature Range		-40		125	°C	
T <sub>C</sub>	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight					160	g

#### SP4 Package outline (dimensions in mm)



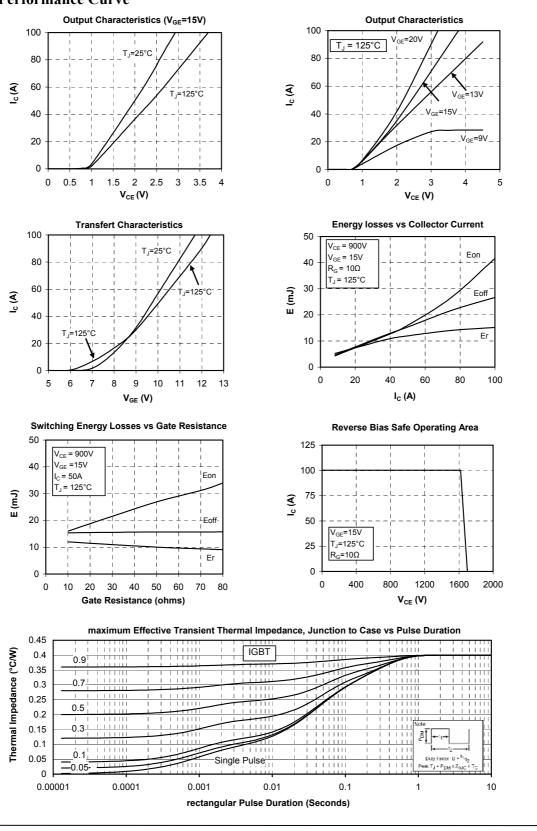
APTGT50H170TG-Rev 2 October, 2012

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#### **Typical Performance Curve**

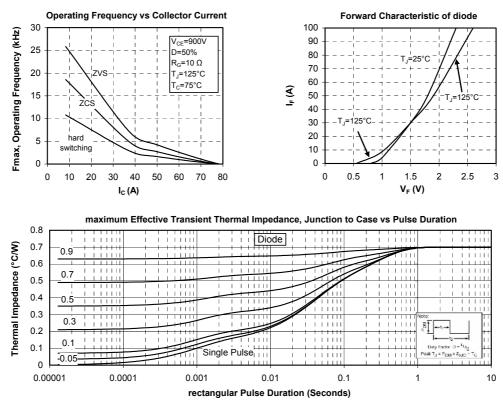
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APTGT50H170TG-Rev 2 October, 2012

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APTGT50H170TG-Rev 2 October, 2012

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5 - 6



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